This technology is currently not available for licensing

Tech ID: 30116

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation
- Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
- A Structure For Increasing Mobility In A High-Electron-Mobility Transistor
- Ultraviolet Laser Diode on Nano-Porous AlGaN template
- Improved Reliability & Enhanced Performance of III-Nitride Tunnel Junction Optoelectronic Devices
- (In,Ga,Al)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- Thermally Stable, Laser-Driven White Lighting Device
- GaN-based Vertical Metal Oxide Semiconductor and Junction Field Effect Transistors
- Methods for Fabricating III-Nitride Tunnel Junction Devices
- Contact Architectures for Tunnel Junction Devices
- III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
- Iii-N Transistor With Stepped Cap Layers
- A Method To Lift-Off Nitride Materials With Electrochemical Etch
- High-Intensity Solid State White Laser Diode
- Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
- III-N Based Material Structures and Circuit Modules Based on Strain Management

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